

MOSFET

OptiMOS™5 Power-Transistor, 100 V

Features

- Optimized for high performance SMPS, e.g. sync. Rec.
- 100% avalanche tested
- Superior thermal resistance
- N-channel, logic level
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Qualified according to JEDEC Standard

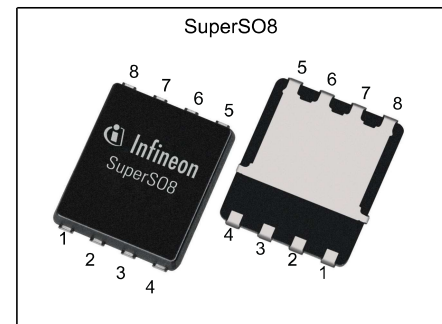
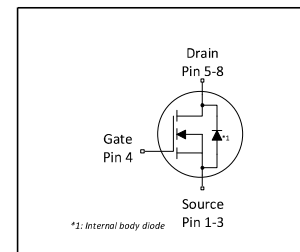


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	7	m Ω
I_D	79	A
Q_{oss}	41	nC
$Q_G(0V..4.5V)$	16	nC



RoHS

Type / Ordering Code	Package	Marking	Related Links
BSC0805LS	PG-TDSON-8	0805LS	-



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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	79 61 14	A	$V_{GS}=10\text{ V}$, $T_C=25\text{ °C}$ $V_{GS}=10\text{ V}$, $T_C=100\text{ °C}$ $V_{GS}=10\text{ V}$, $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}^1)$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	318	A	$T_A=25\text{ °C}$
Avalanche energy, single pulse ³⁾	E_{AS}	-	-	55	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	83 2.5	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$, $R_{thJA}=50\text{ °C/W}^2)$
Operating and storage temperature	T_j , T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	0.9	1.5	°C/W	-
Device on PCB, 6 cm ² cooling area ¹⁾	R_{thJA}	-	-	50	°C/W	-

¹⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

²⁾ See Diagram 3 for more detailed information

³⁾ See Diagram 13 for more detailed information

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	1.1	1.7	2.3	V	$V_{DS}=V_{GS}$, $I_D=49\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	6.0 7.7	7.0 8.5	m Ω	$V_{GS}=10\text{ V}$, $I_D=40\text{ A}$ $V_{GS}=4.5\text{ V}$, $I_D=20\text{ A}$
Gate resistance ¹⁾	R_G	-	1.0	1.5	Ω	-
Transconductance	g_{fs}	36	73	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$, $I_D=40\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹⁾	C_{iss}	-	2100	2700	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	340	440	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ¹⁾	C_{rss}	-	16	28	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	6.5	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Rise time	t_r	-	3.6	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	20	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Fall time	t_f	-	5.3	-	ns	$V_{DD}=40\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=50\text{ A}$, $R_{G,ext}=3\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	7	-	nC	$V_{DD}=50\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge at threshold	$Q_{g(th)}$	-	4	-	nC	$V_{DD}=50\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate to drain charge ¹⁾	Q_{gd}	-	6	8	nC	$V_{DD}=50\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Switching charge	Q_{sw}	-	9	-	nC	$V_{DD}=50\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total ¹⁾	Q_g	-	16	20	nC	$V_{DD}=50\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	3.2	-	V	$V_{DD}=50\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	26	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ¹⁾	Q_{oss}	-	41	54	nC	$V_{DS}=50\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test.

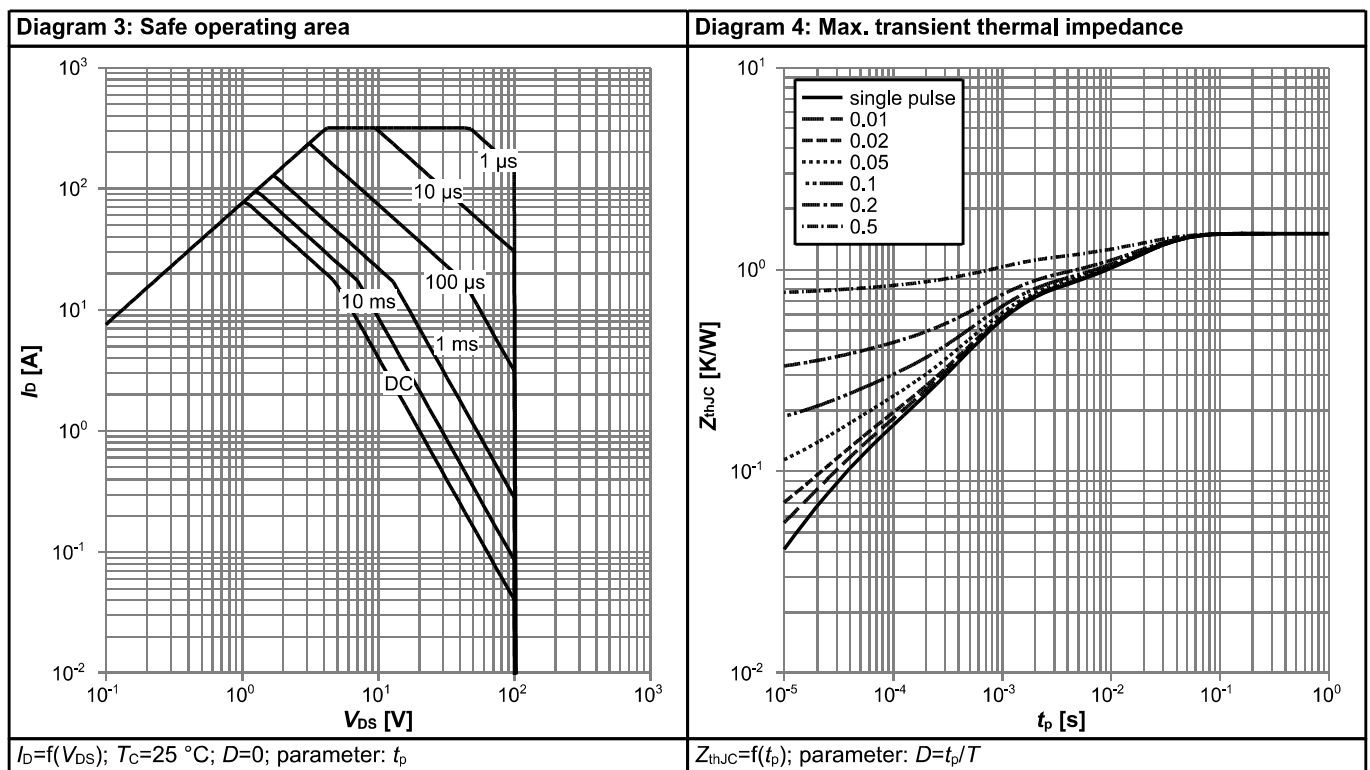
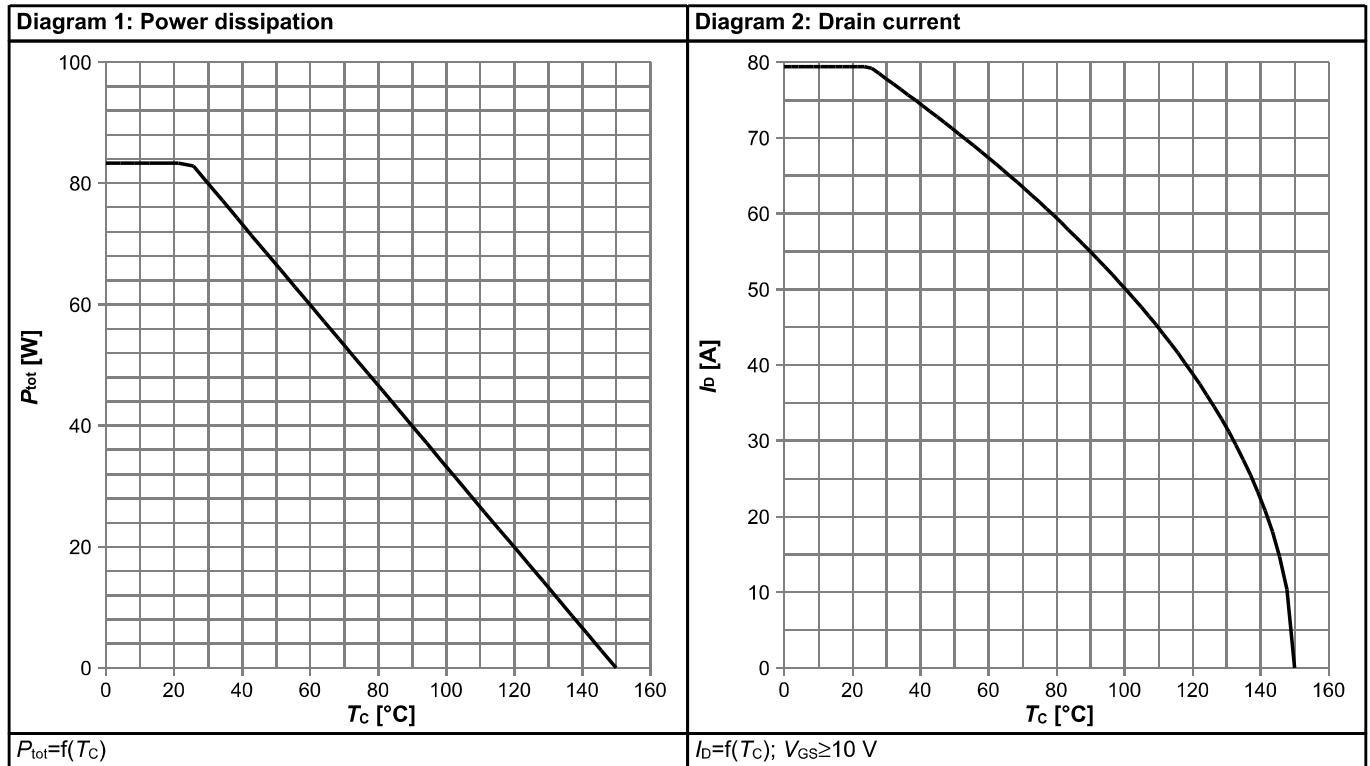
²⁾ See "Gate charge waveforms" for parameter definition

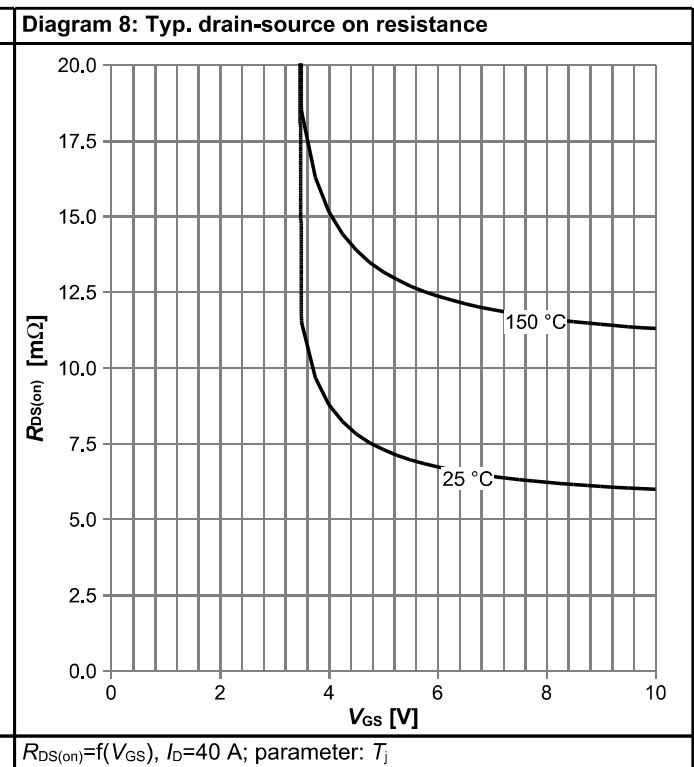
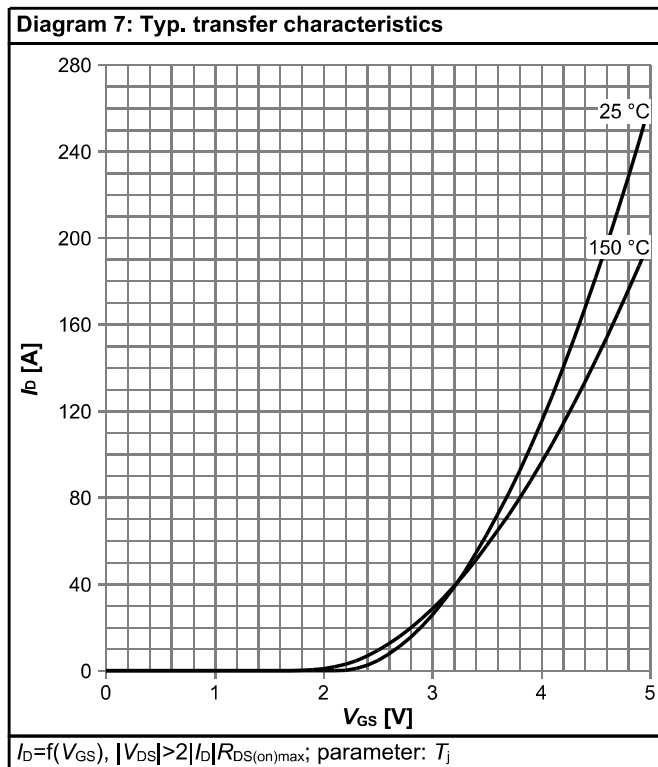
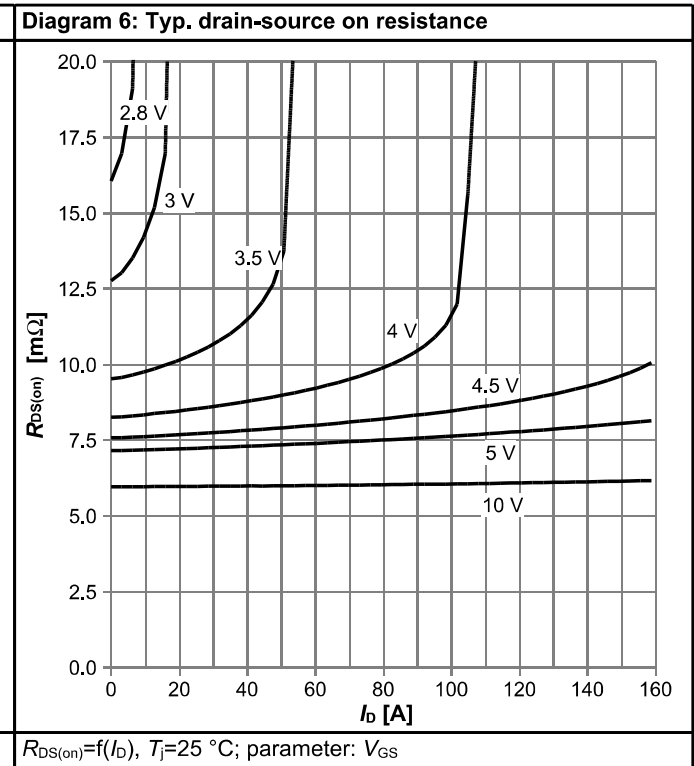
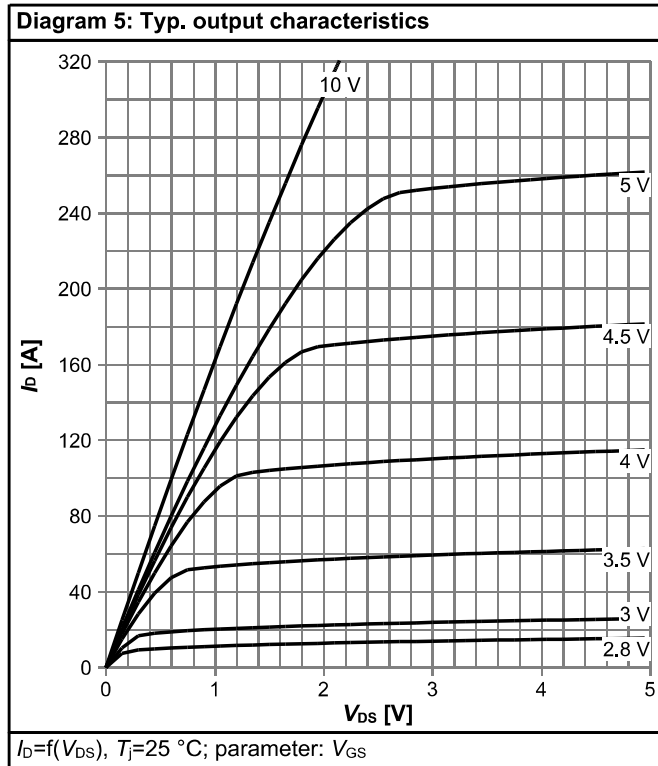
Table 7 Reverse diode

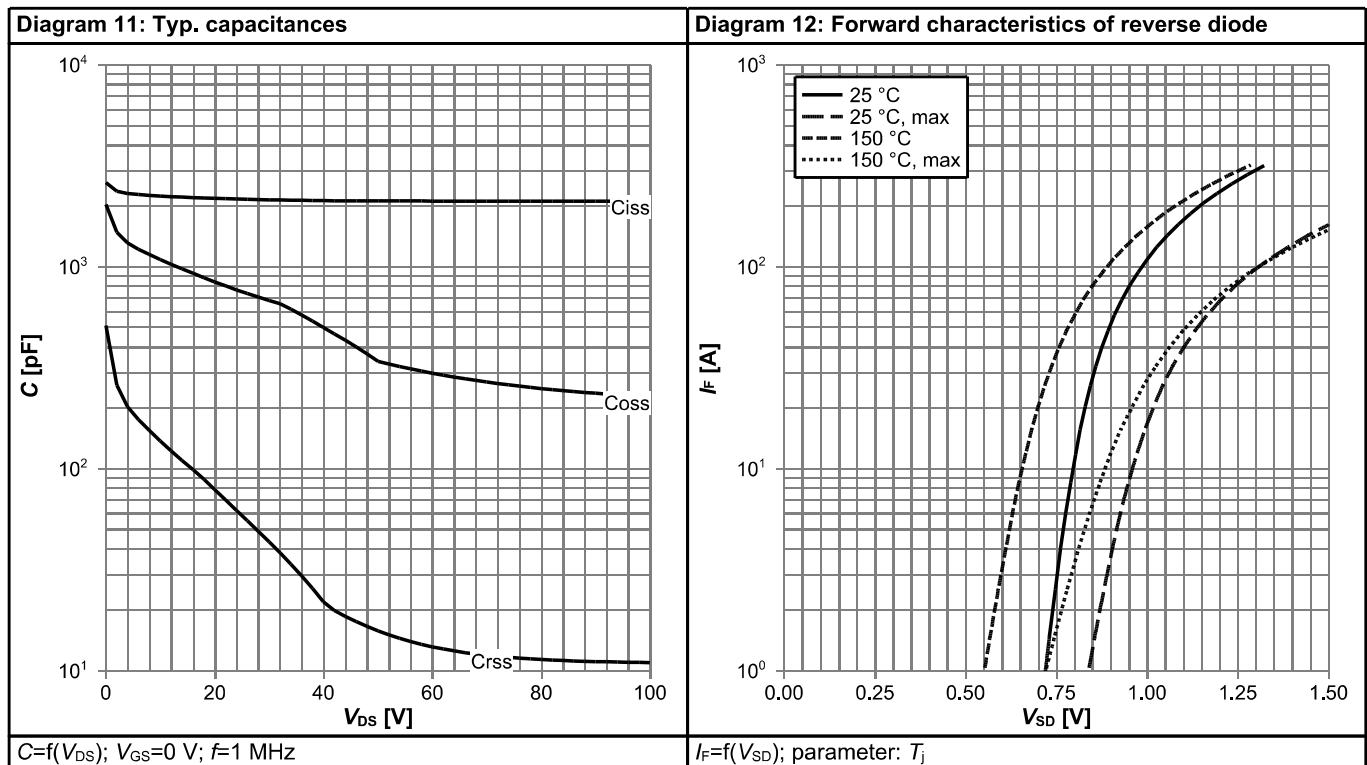
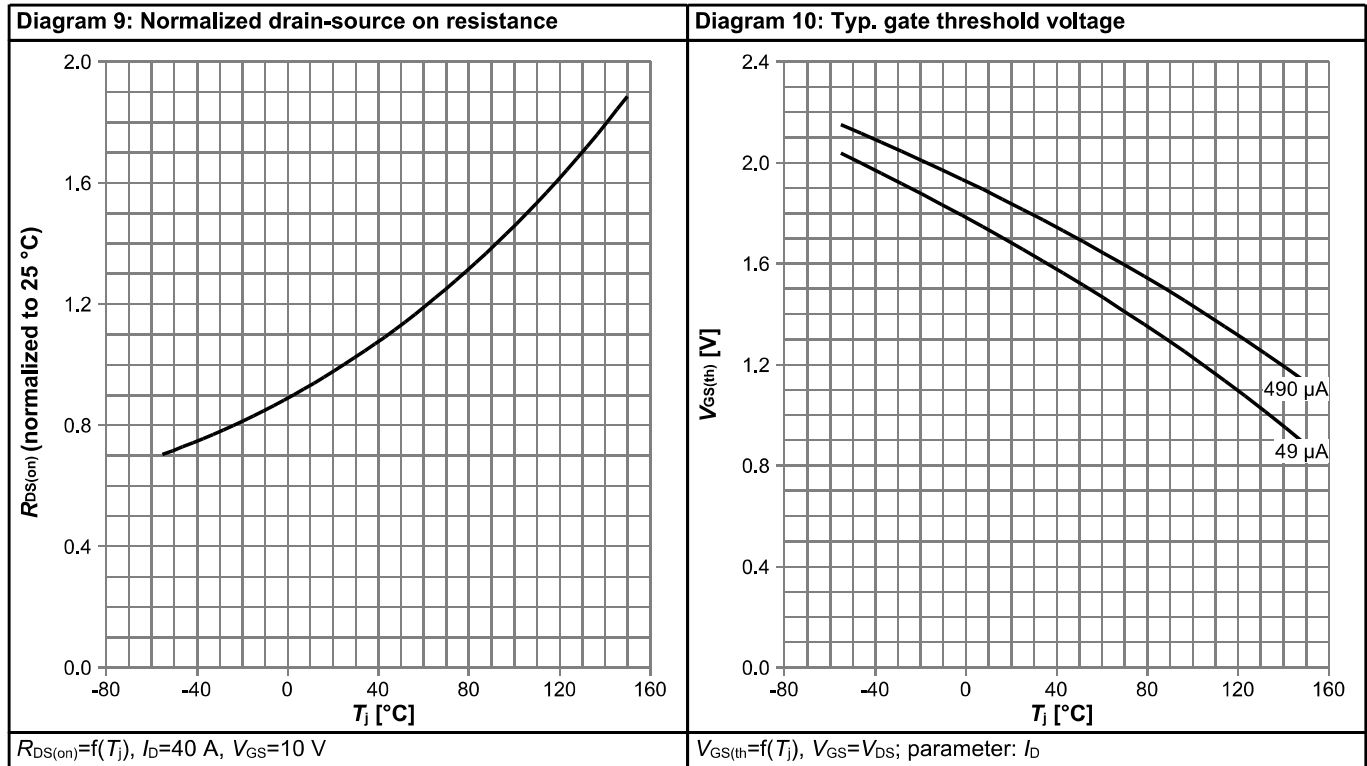
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	70	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	318	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.9	1.1	V	$V_{GS}=0\text{ V}, I_F=40\text{ A}, T_J=25\text{ °C}$
Reverse recovery time ¹⁾	t_{rr}	-	21	42	ns	$V_R=50\text{ V}, I_F=40\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	12	24	nC	$V_R=50\text{ V}, I_F=40\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$

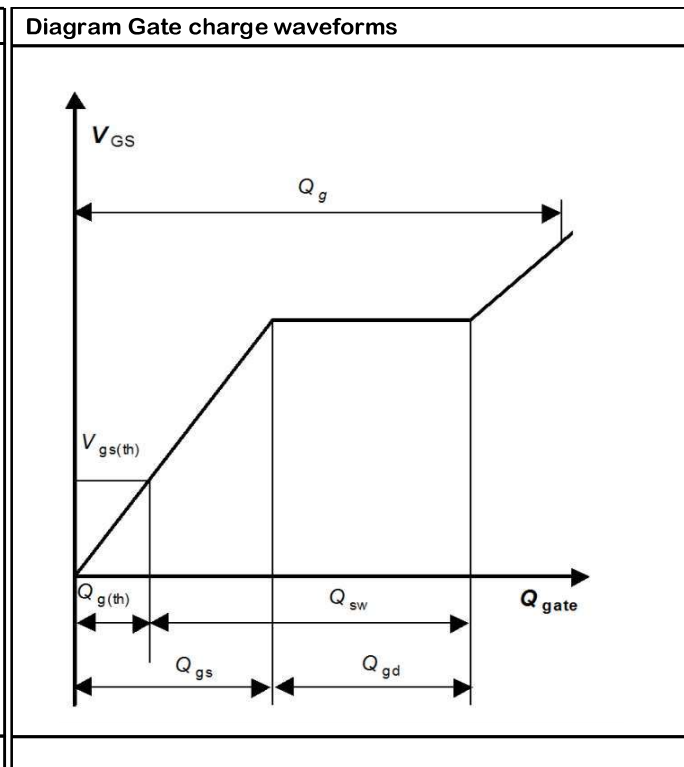
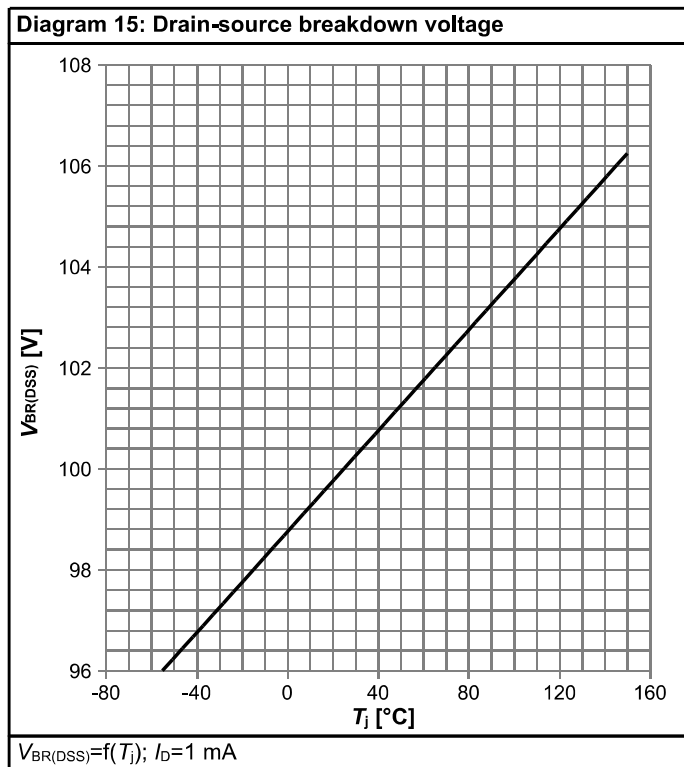
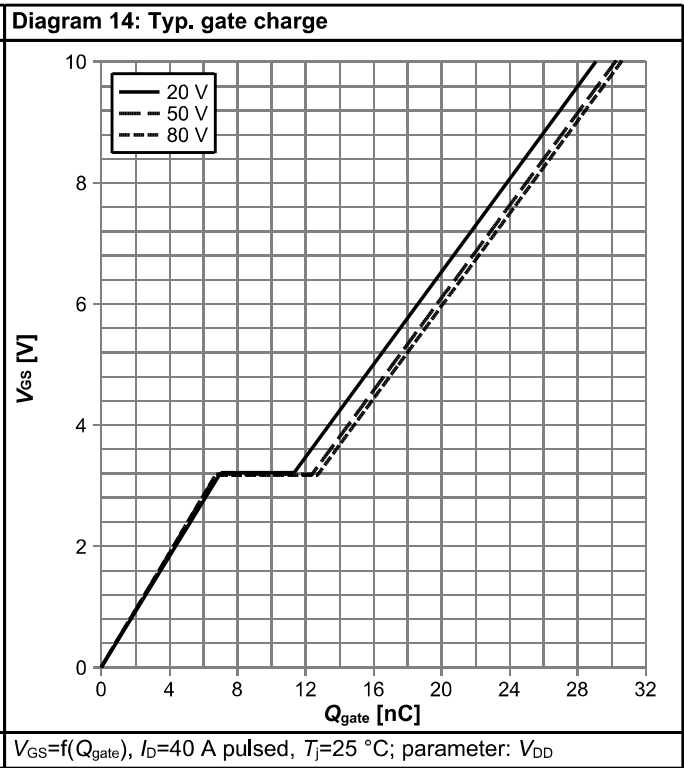
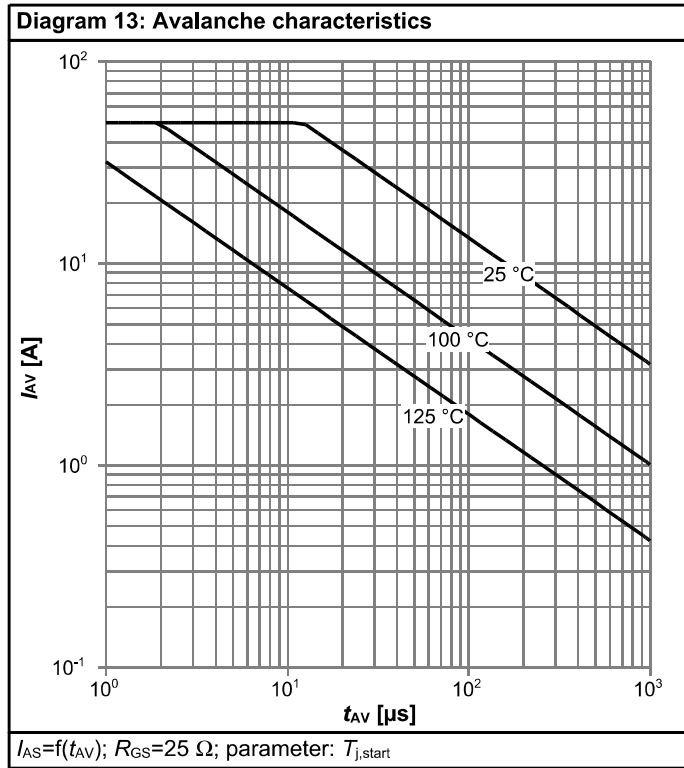
¹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

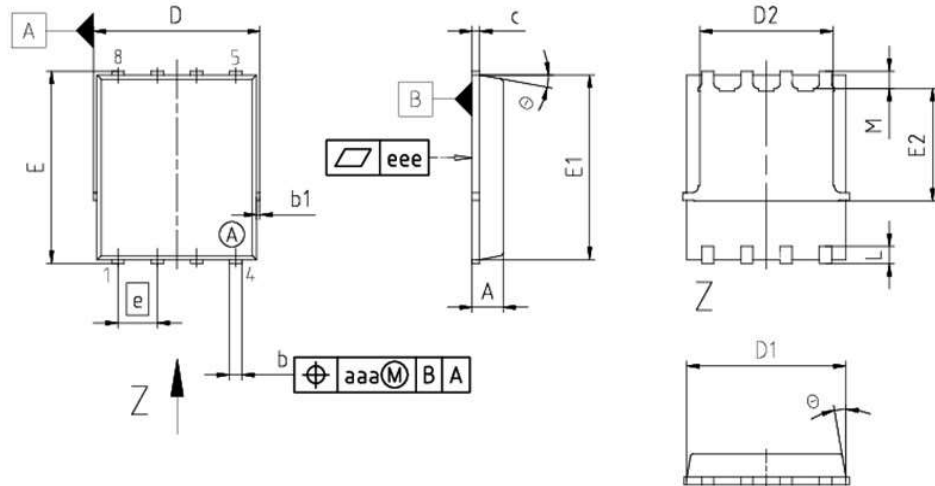








5 Package Outlines



DIM	MILLIMETERS	
	MIN	MAX
A	0.90	1.10
b	0.31	0.54
b1	0.02	0.22
c	0.15	0.35
D	5.15	5.49
D1	4.95	5.35
D2	3.70	4.40
E	5.95	6.35
E1	5.70	6.10
E2	3.40	3.80
e	1.27	
N	8	
L	0.45	0.71
M	0.45	0.75
ϕ	8.5°	12°
aaa	0.25	
eee	0.08	

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ISSUE DATE 10-04-2013
REVISION 04

Figure 1 Outline PG-TDSON-8, dimensions in mm

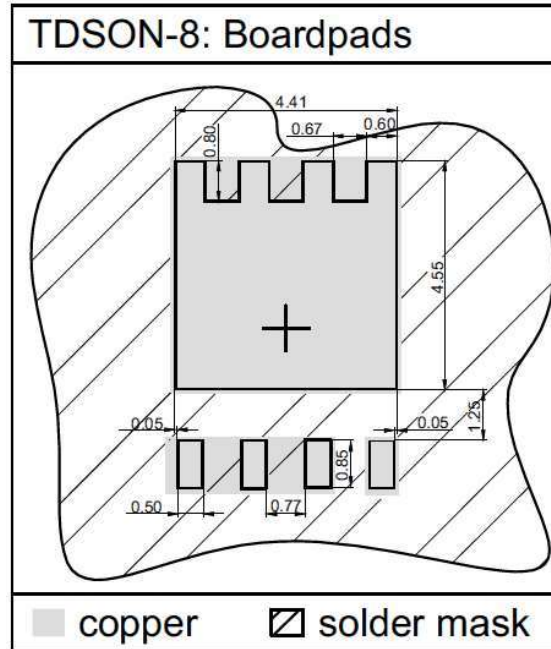


Figure 2 Outline Footprint (TDSON-8)

Revision History

BSC0805LS

Revision: 2021-12-06, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2019-04-03	Release of final version
2.1	2021-12-06	Update "Avalanche energy"

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